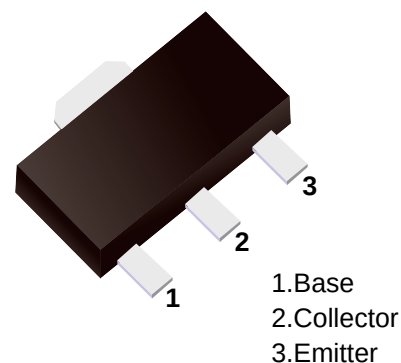


2SD882

■ NPN Transistors

■ Features

- Excellent h_{FE} linearity and high h_{FE}
 $h_{FE} = 60$ to 400 ($V_{CE} = 2\text{ V}$, $I_C = 1\text{ A}$)



■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current to Continuous	I_C	3	A
Collector Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

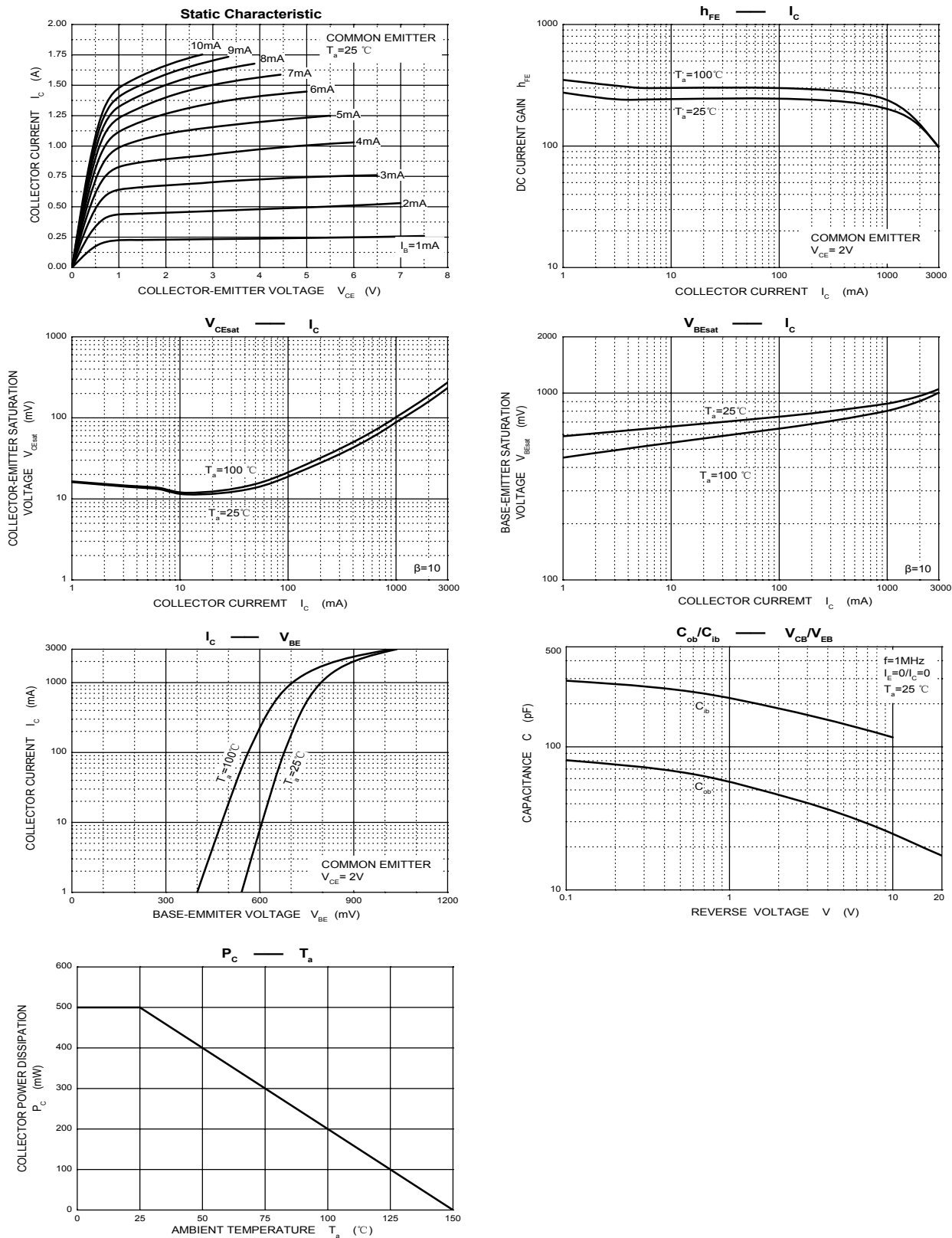
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu\text{A}$, $I_E=0$	40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=10\text{ mA}$, $I_B=0$	30			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu\text{A}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{ V}$, $I_E=0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{ V}$, $I_B=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{ V}$, $I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{ V}$, $I_C=1\text{ A}$	60		400	
		$V_{CE}=2\text{ V}$, $I_C=100\text{ mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{ A}$, $I_B=0.2\text{ A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{ A}$, $I_B=0.2\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{ V}$, $I_C=0.1\text{ mA}$, $f=10\text{ MHz}$	50			MHz

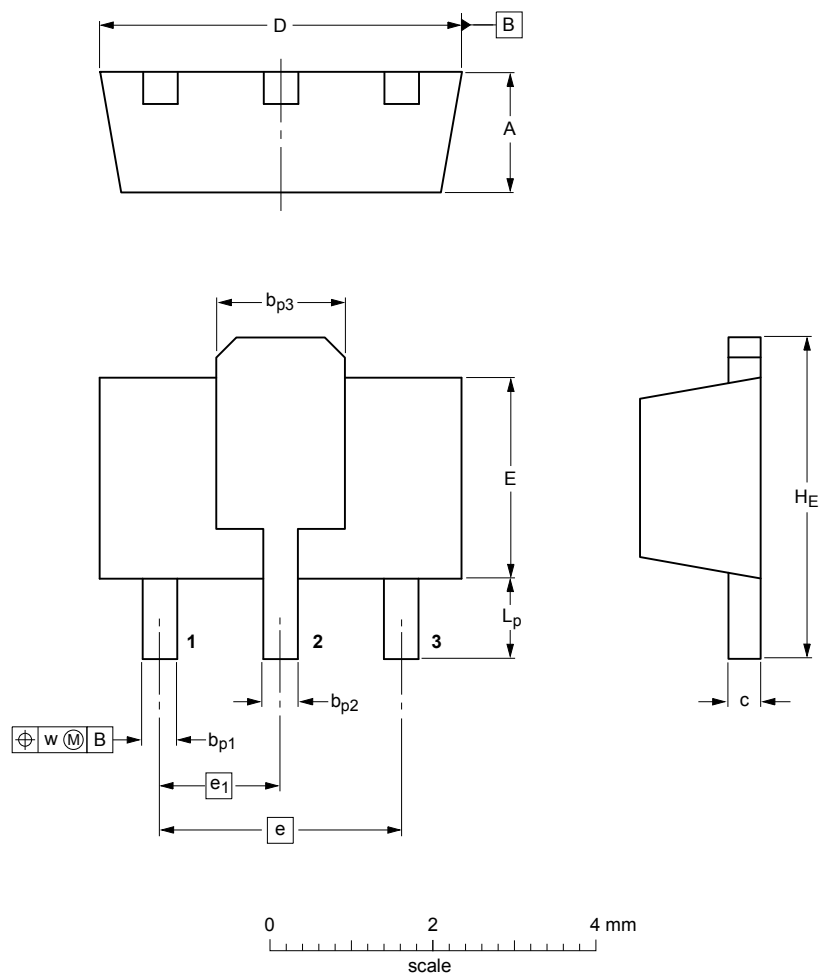
■ Classification of $h_{FE}(1)$

Type	2SD882-R	2SD882-Q	2SD882-P	2SD882-E
Range	60-120	100-200	160-320	200-400
Marking	882R	882Q	882P	882E

■ Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13